

# SKKT 132 H4, SKKH 132 H4



**SEMIPACK® 2**

## Thyristor / Diode Modules

**SKKH 132 H4**

**SKKT 132 H4**

### Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

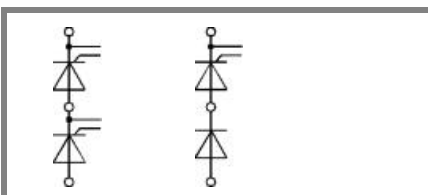
### Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

$V_{RSM}$ V	$V_{RRM}, V_{DRM}$ V	$I_{TRMS} = 220$ A (maximum value for continuous operation) $I_{TAV} = 132$ A (sin. 180; $T_c = 84$ °C)	
2100	2000	SKKT 132/20E H4	SKKH 132/20E H4
2300	2200	SKKT 132/22E H4	SKKH 132/22E H4

Symbol	Conditions	Values	Units
$I_{TAV}$	sin. 180; $T_c = 85$ (100) °C;	128 (90)	A
$I_{TSM}$	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 125$ °C; 10 ms	4500 3800	A A
$i^2t$	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 125$ °C; 8,3 ... 10 ms	100000 72000	A <sup>2</sup> s A <sup>2</sup> s
$V_T$	$T_{vj} = 25$ °C; $I_T = 500$ A	max. 1,8	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 1,1	V
$r_T$	$T_{vj} = 125$ °C	max. 2	mΩ
$I_{DD}; I_{RD}$	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 40	mA
$t_{gd}$	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
$t_{gr}$	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 200	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	max. 1000	V/μs
$t_q$	$T_{vj} = 125$ °C	50 ... 150	μs
$I_H$	$T_{vj} = 25$ °C; typ. / max.	150 / 400	mA
$I_L$	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 1000	mA
$V_{GT}$	$T_{vj} = 25$ °C; d.c.	min. 2	V
$I_{GT}$	$T_{vj} = 25$ °C; d.c.	min. 150	mA
$V_{GD}$	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
$I_{GD}$	$T_{vj} = 125$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,17 / 0,085	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,18 / 0,09	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,2 / 0,1	K/W
$R_{th(c-s)}$	per thyristor / per module	0,1 / 0,05	K/W
$T_{vj}$		- 40 ... + 125	°C
$T_{stg}$		- 40 ... + 125	°C
$V_{isol}$	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
$M_s$	to terminal	5 ± 15 % <sup>1)</sup>	Nm
$M_t$	to terminal	5 ± 15 %	Nm
a		5 * 9,81	m/s <sup>2</sup>
m	approx.	175	g
Case	SKKT SKKH	A 21 A 22	



SKKT

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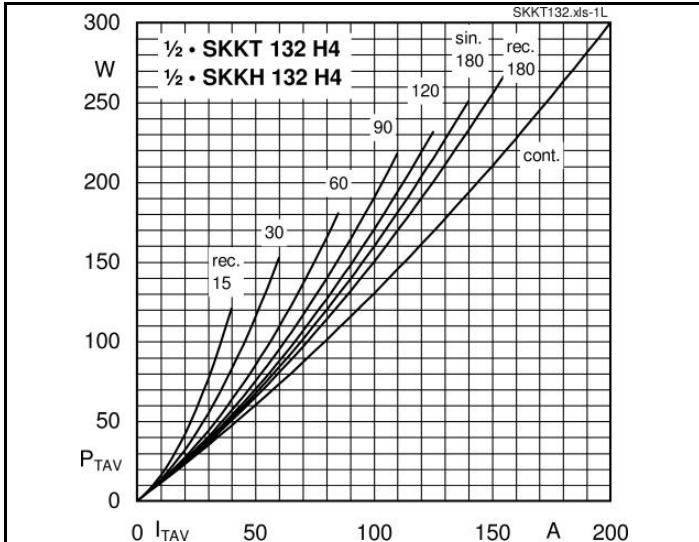


Fig. 1L Power dissipation per thyristor vs. on-state current

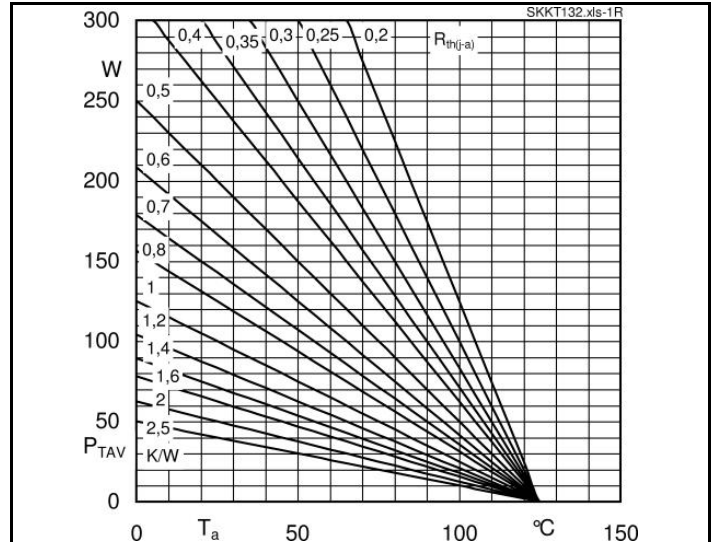


Fig. 1R Power dissipation per thyristor vs. ambient temp.

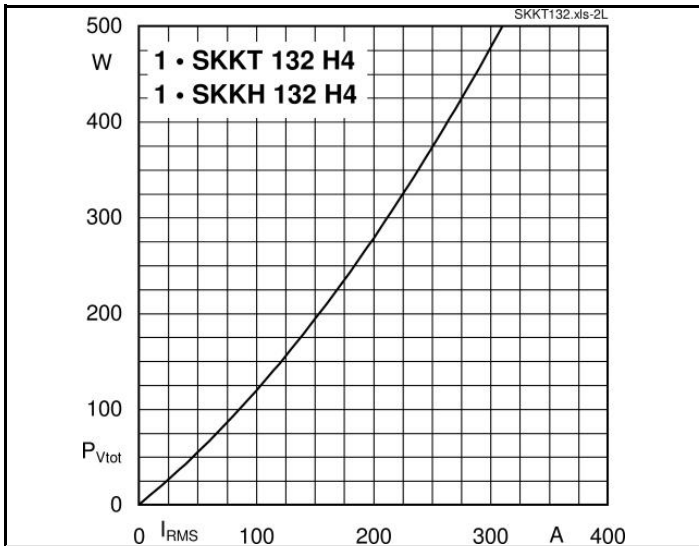


Fig. 2L Power dissipation per module vs. rms current

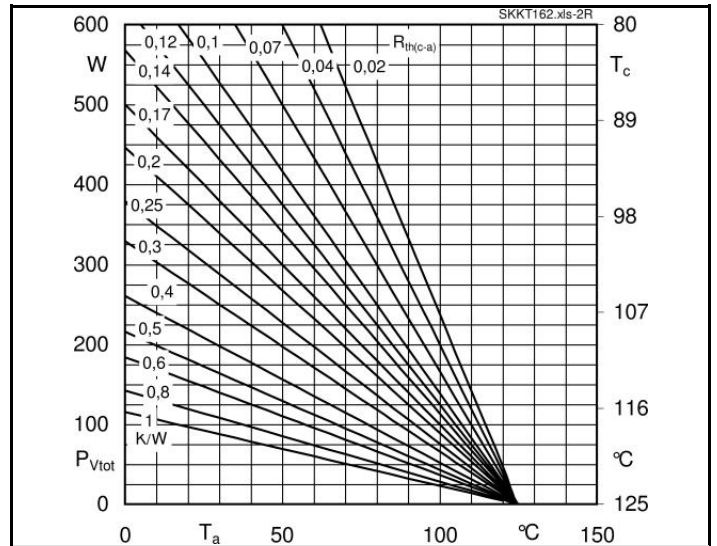


Fig. 2R Power dissipation per module vs. case temp.

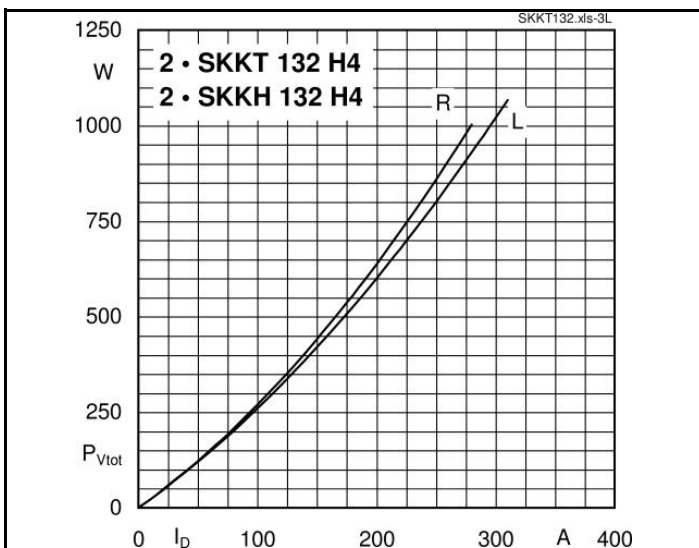


Fig. 3L Power dissipation of two modules vs. direct current

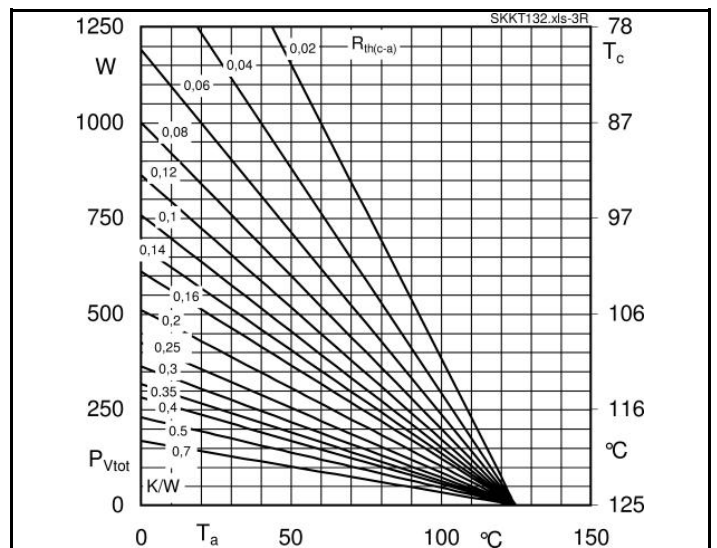
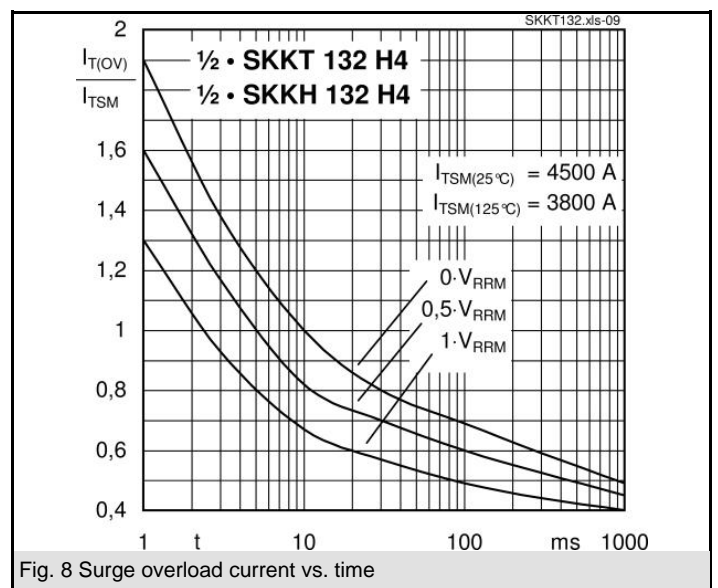
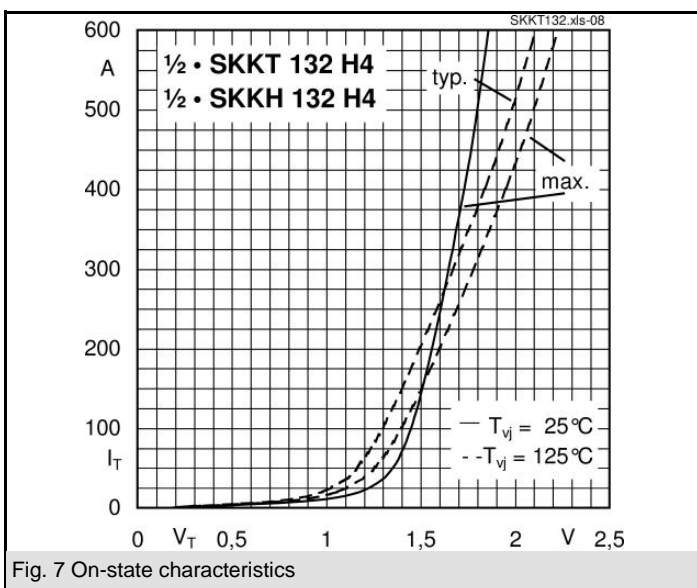
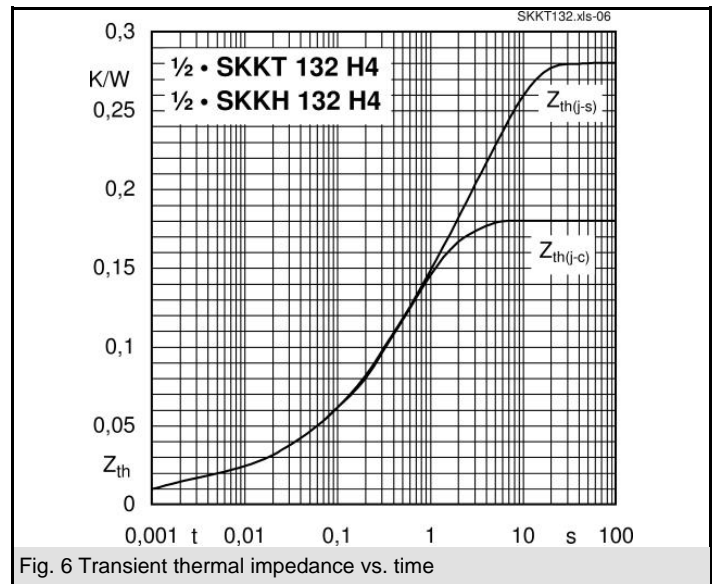
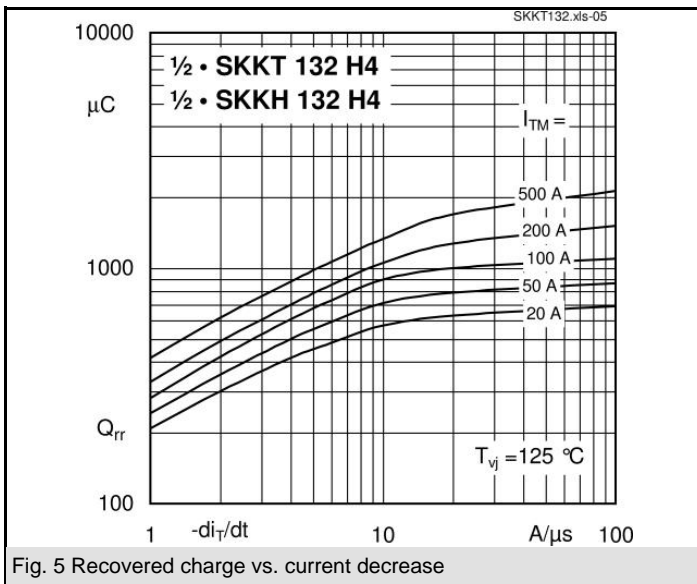
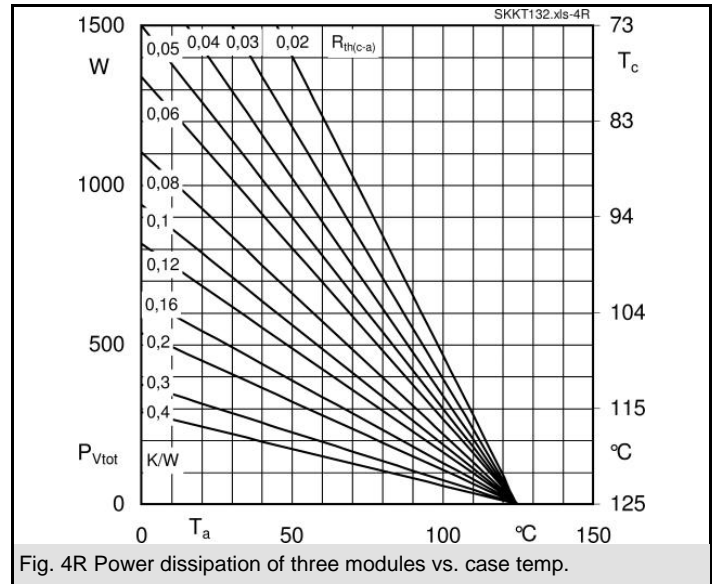
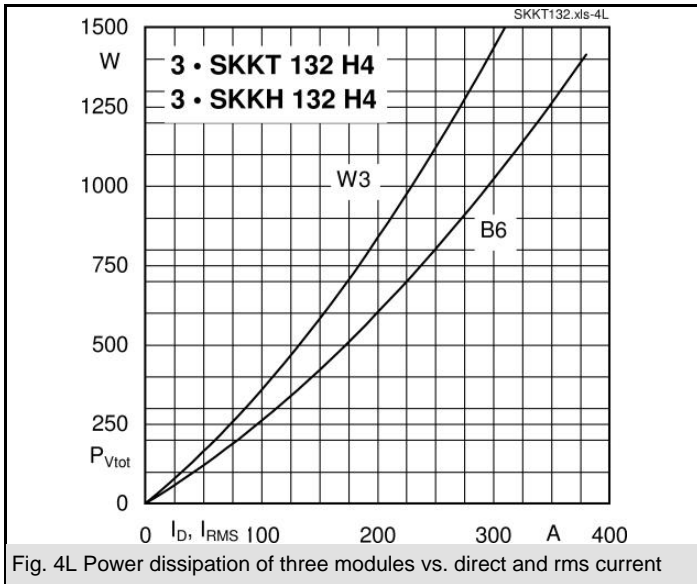


Fig. 3R Power dissipation of two modules vs. case temp.

# SKKT 132 H4, SKKH 132 H4



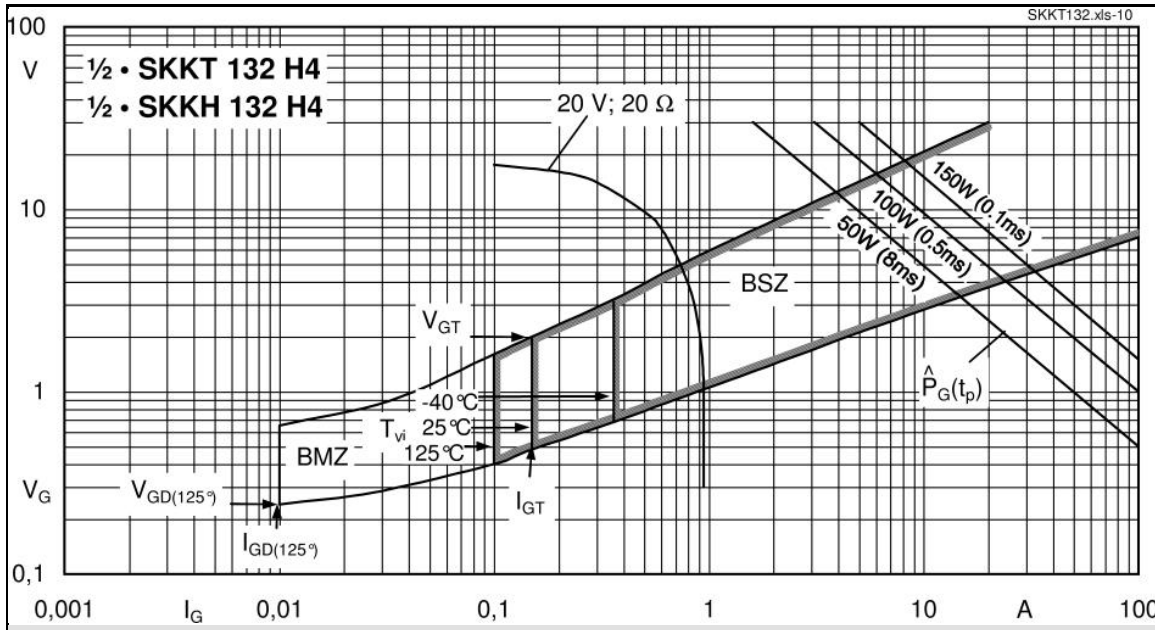
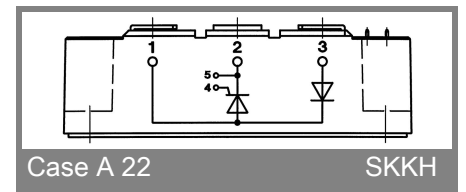
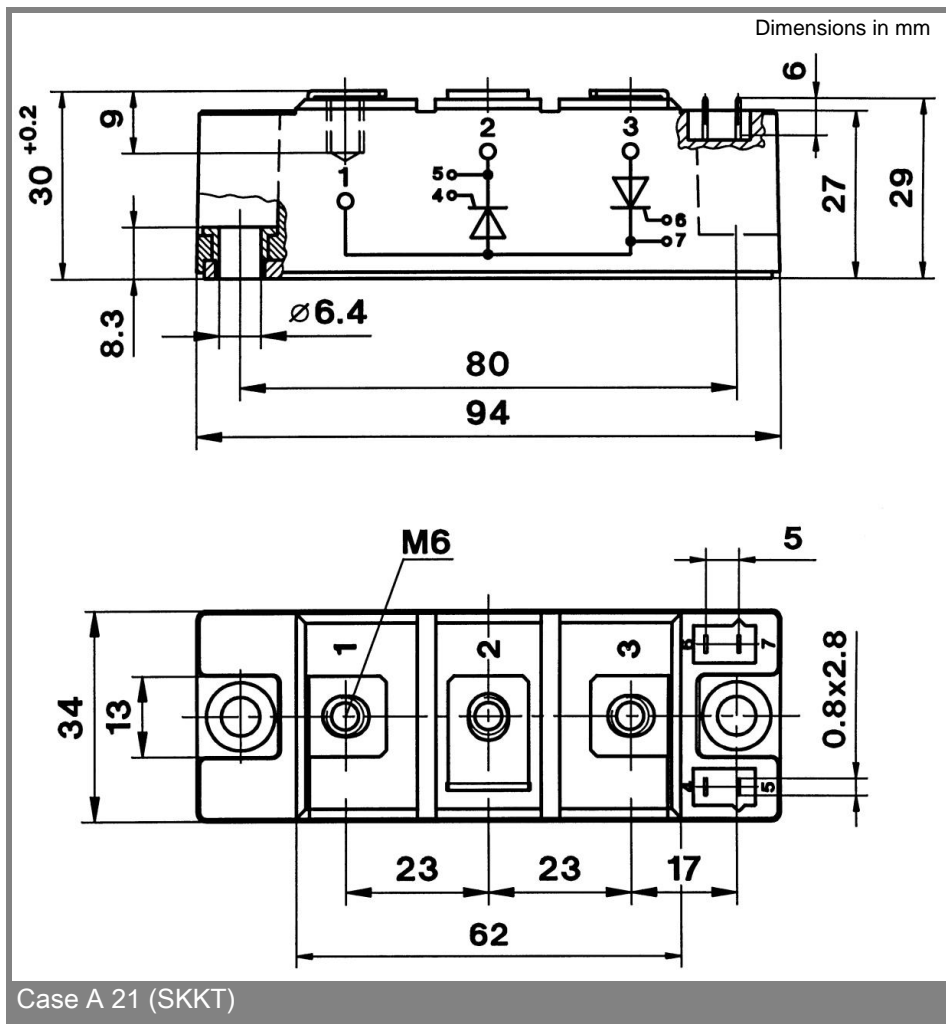


Fig. 9 Gate trigger characteristics



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